

METHOD OF FORMING A CAPACITOR STRUCTURE

ABSTRACT OF THE DISCLOSURE

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A capacitor structure and method of forming it are described. In particular, a high-K dielectric oxide is provided as the capacitor dielectric. The high-K dielectric is deposited in a series of thin layers and oxidized in a series of oxidation steps, as opposed to a depositing a single thick layer. Further, at least one of the oxidation steps is less
10 aggressive than the oxidation environment or environments that would be used to deposit the single thick layer. This allows greater control over oxidizing the dielectric and other components beyond the dielectric.